MJE243 (NPN), MJE253 (PNP)

Complementary Silicon Power Plastic Transistors

These devices are designed for low power audio amplifier and low−current, high−speed switching applications.

Features

- High Collector−Emitter Sustaining Voltage
- High DC Current Gain
- Low Collector−Emitter Saturation Voltage
- High Current Gain Bandwidth Product
- Annular Construction for Low Leakages
- These Devices are Pb−Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage	V_{CEO}	100	Vdc
Collector−Base Voltage	V_{CB}	100	Vdc
Emitter−Base Voltage	V_{EB}	7.0	Vdc
Collector Current − Continuous	I_C	4.0	Adc
Collector Current − Peak	I_{CM}	8.0	Adc
Base Current	I_B	10	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	15 120	W mW/°C
Total Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Case	θ_{JC}	8.34	°C/W
Thermal Resistance, Junction−to−Ambient	θ_{JA}	83.4	°C/W

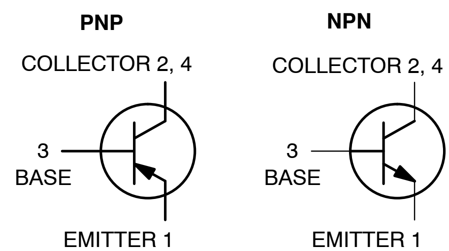
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

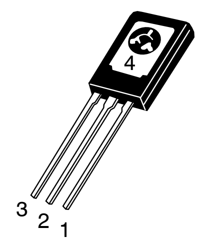
ON Semiconductor®

http://onsemi.com

**4.0 AMPERES
POWER TRANSISTORS
COMPLEMENTARY SILICON
100 VOLTS, 15 WATTS**

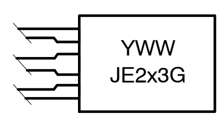
SCHEMATIC





**TO−225
CASE 77−09
STYLE 1**

MARKING DIAGRAM



Y = Year
WW = Work Week
JE2x3 = Device Code
x = 4 or 5
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJE243G	TO−225 (Pb−Free)	500 Units/Box
MJE253G	TO−225 (Pb−Free)	500 Units/Box

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Sustaining Voltage (I_C = 10 mAdc, I_B = 0)	$V_{CEO(sus)}$	100	–	V
Collector Cutoff Current	I_{CBO}			
(V_{CB} = 100 Vdc, I_E = 0)		–	0.1	μA
(V_{CE} = 100 Vdc, I_E = 0, T_C = 125°C)		–	0.1	mA
Emitter Cutoff Current (V_{BE} = 7.0 Vdc, I_C = 0)	I_{EBO}	–	0.1	μAdc
ON CHARACTERISTICS				
DC Current Gain	h_{FE}			–
(I_C = 200 mAdc, V_{CE} = 1.0 Vdc)		40	180	
(I_C = 1.0 Adc, V_{CE} = 1.0 Vdc)		15	–	
Collector−Emitter Saturation Voltage	$V_{CE(sat)}$			V
(I_C = 500 mAdc, I_B = 50 mAdc)		–	0.3	
(I_C = 1.0 Adc, I_B = 100 mAdc)		–	0.6	
Base−Emitter Saturation Voltage (I_C = 2.0 Adc, I_B = 200 mAdc)	$V_{BE(sat)}$	–	1.8	V
Base−Emitter On Voltage (I_C = 500 mAdc, V_{CE} = 1.0 Vdc)	$V_{BE(on)}$	–	1.5	V
DYNAMIC CHARACTERISTICS				
Current−Gain − Bandwidth Product (I_C = 100 mAdc, V_{CE} = 10 Vdc, f_{test} = 10 MHz)	f_T	40	–	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 0.1 MHz)	C_{ob}	–	50	pF

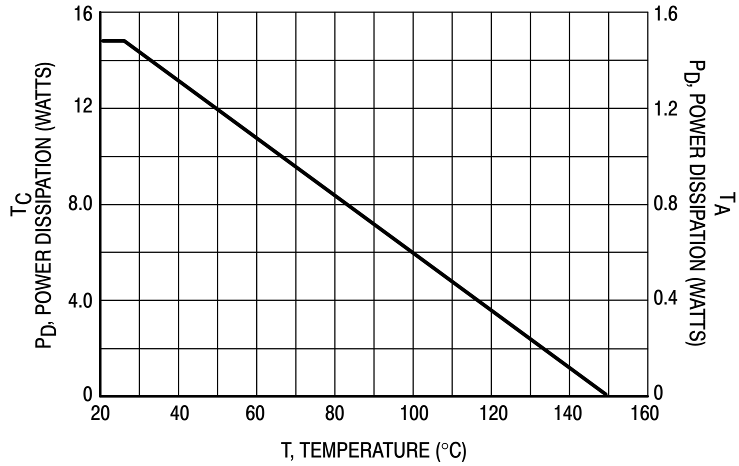


Figure 1. Power Derating

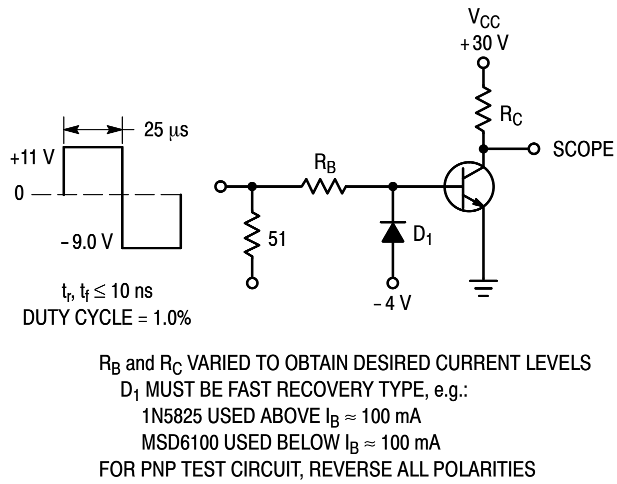


Figure 2. Switching Time Test Circuit

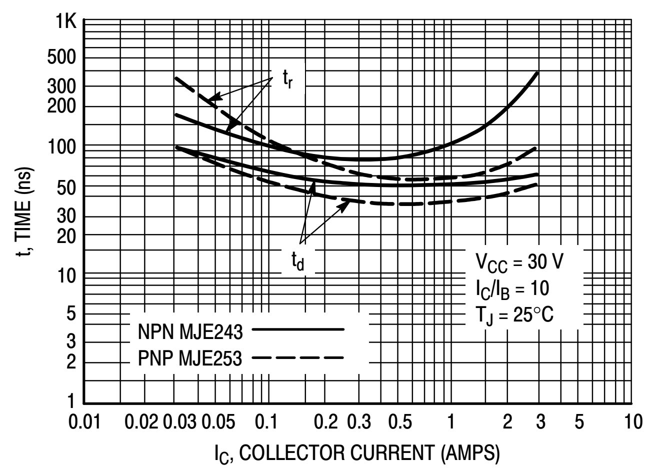


Figure 3. Turn−On Time

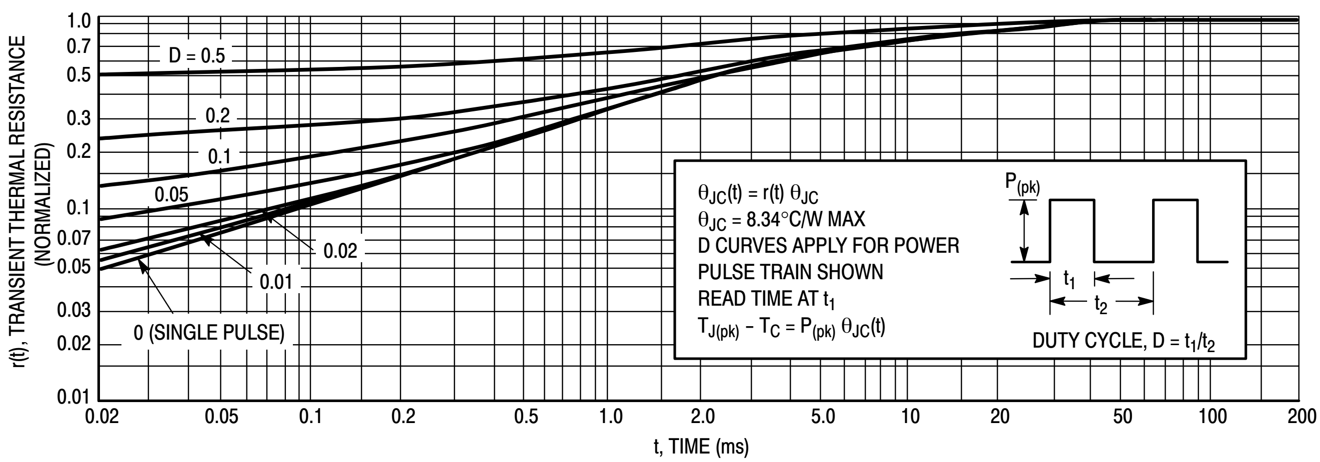


Figure 4. Thermal Response

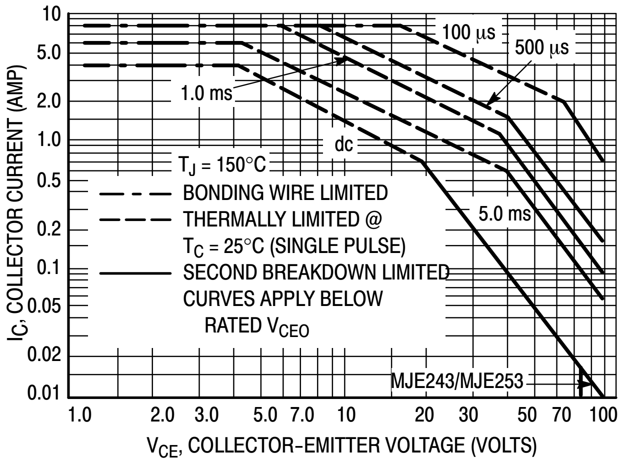


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150°C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150°C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

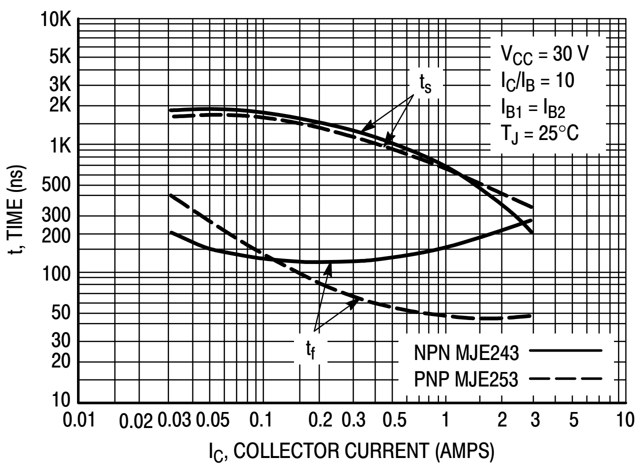


Figure 6. Turn−Off Time

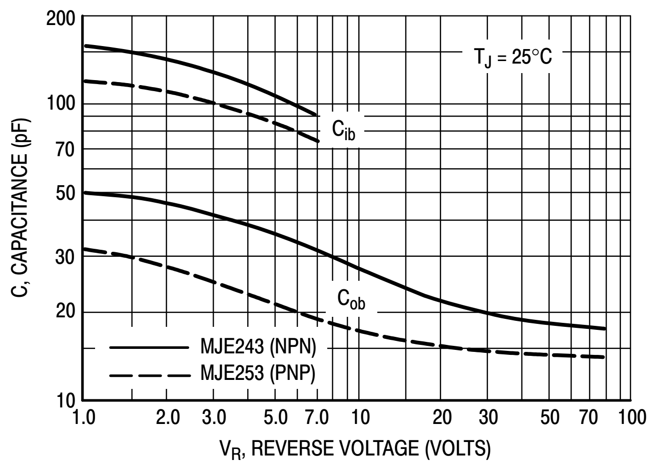


Figure 7. Capacitance

NPN
MJE243

PNP
MJE253

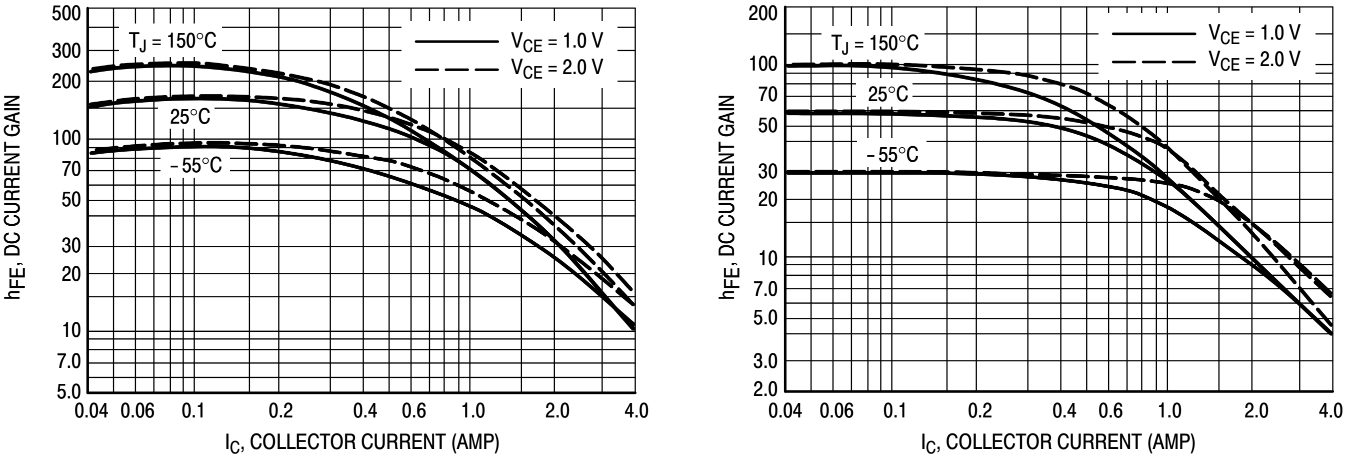


Figure 8. DC Current Gain

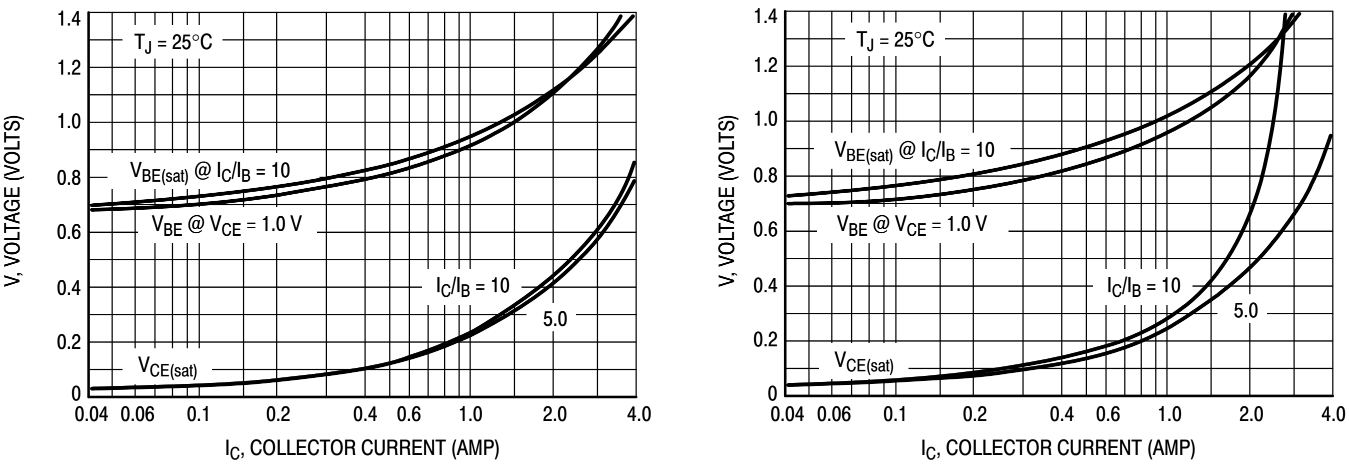


Figure 9. “On” Voltages

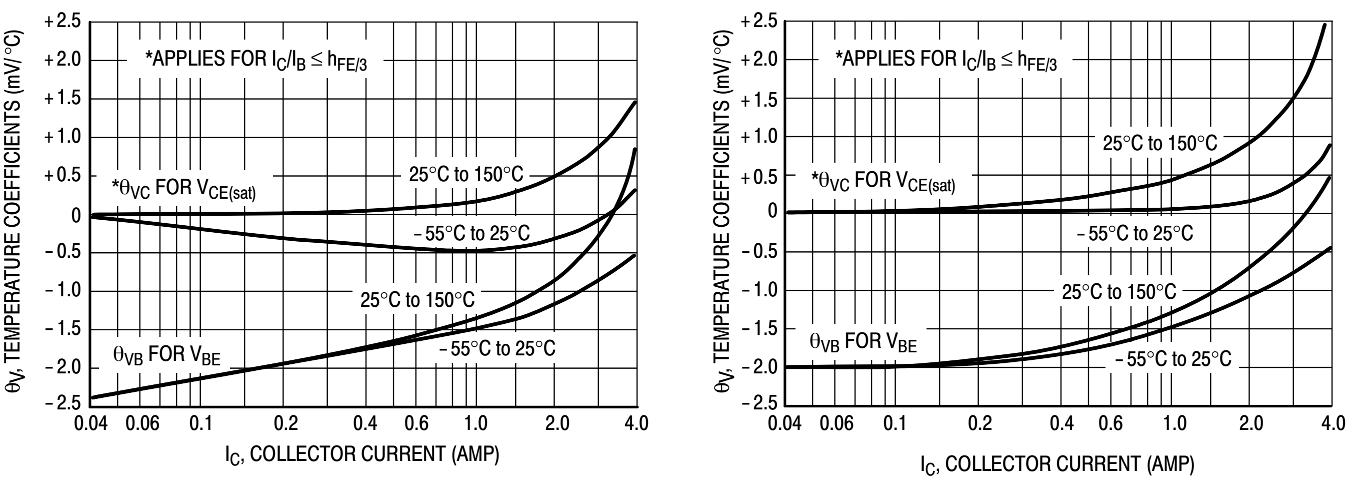
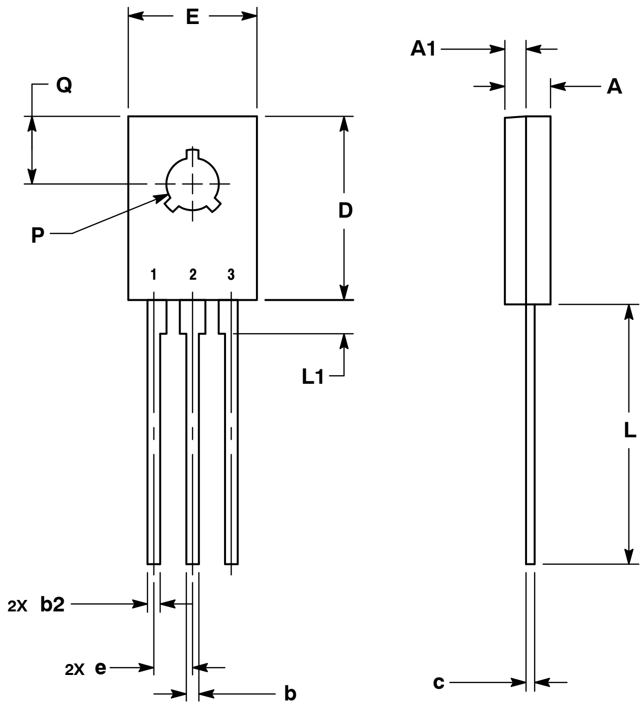


Figure 10. Temperature Coefficients

PACKAGE DIMENSIONS

TO−225
CASE 77−09
ISSUE AA



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS	
DIM	MIN	MAX
A	2.40	3.00
A1	1.00	1.50
b	0.60	0.90
b2	0.51	0.88
c	0.39	0.63
D	10.60	11.10
E	7.40	7.80
e	2.04	2.54
L	14.50	16.63
L1	1.27	2.54
P	2.90	3.30
Q	3.80	4.20

PUBLICATION ORDERING INFORMATION

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